Ronald D Schrimpf

List of Publications by Year
in descending order

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676	19,823	67	99
papers	citations	h-index	g-index
		15880	38517

678	678	678	6062
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Analysis of Heavy-Ion-Induced Leakage Current in SiC Power Devices. IEEE Transactions on Nuclear Science, 2022, 69, 248-253.	1.2	4
2	Effects of Layer-to-Layer Coupling on the Total-Ionizing-Dose Response of 3-D-Sequentially Integrated FD-SOI MOSFETs. IEEE Transactions on Nuclear Science, 2022, 69, 1420-1427.	1.2	3
3	Total-Ionizing-Dose Effects on Polycrystalline-Si Channel Vertical-Charge-Trapping Nand Devices. IEEE Transactions on Nuclear Science, 2022, 69, 314-320.	1.2	4
4	TID Effects in Highly Scaled Gate-All-Around Si Nanowire CMOS Transistors Irradiated to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2022, 69, 1444-1452.	1.2	11
5	Negative-Bias-Stress and Total-Ionizing-Dose Effects in Deeply Scaled Ge-GAA Nanowire pFETs. IEEE Transactions on Nuclear Science, 2022, 69, 299-306.	1.2	1
6	Radiation Effects in AlGaN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2022, 69, 1105-1119.	1.2	32
7	Effects of Ion-Induced Displacement Damage on GaN/AlN MEMS Resonators. IEEE Transactions on Nuclear Science, 2022, 69, 216-224.	1.2	4
8	Radiation-Induced Transient Response Mechanisms in Photonic Waveguides. IEEE Transactions on Nuclear Science, 2022, 69, 546-557.	1.2	2
9	Simulation of Pulsed Laser-Induced Testing in Microelectronic Devices. IEEE Transactions on Nuclear Science, 2021, , 1-1.	1.2	2
10	Impact of Surface Recombination on Single-Event Charge Collection in an SOI Technology. IEEE Transactions on Nuclear Science, 2021, 68, 305-311.	1.2	7
11	3-D Full-Band Monte Carlo Simulation of Hot-Electron Energy Distributions in Gate-All-Around Si Nanowire MOSFETs. IEEE Transactions on Electron Devices, 2021, 68, 2556-2563.	1.6	11
12	Impacts of Through-Silicon Vias on Total-Ionizing-Dose Effects and Low-Frequency Noise in FinFETs. IEEE Transactions on Nuclear Science, 2021, 68, 740-747.	1.2	10
13	Total Ionizing Dose Responses of 22-nm FDSOI and 14-nm Bulk FinFET Charge-Trap Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 677-686.	1.2	13
14	Total-Ionizing-Dose Response of Highly Scaled Gate-All-Around Si Nanowire CMOS Transistors. IEEE Transactions on Nuclear Science, 2021, 68, 687-696.	1.2	17
15	Modeling COTS System TID Response With Monte Carlo Sampling and Transistor Swapping Experiments. IEEE Transactions on Nuclear Science, 2021, 68, 1008-1013.	1.2	0
16	Observation of Low-Energy Proton Direct Ionization in a 72-Layer 3-D NAND Flash Memory. IEEE Transactions on Nuclear Science, 2021, 68, 835-841.	1.2	5
17	Charge Trapping and Transconductance Degradation in Irradiated 3-D Sequentially Integrated FDSOI MOSFETs. IEEE Transactions on Nuclear Science, 2021, 68, 707-715.	1.2	5
18	Single-Event-Induced Charge Collection in Ge-Channel pMOS FinFETs. IEEE Transactions on Nuclear Science, 2021, 68, 807-814.	1.2	3

#	Article	IF	Citations
19	Comparison of Single-Event Transients in an Epitaxial Silicon Diode Resulting From Heavy-Ion-, Focused X-Ray-, and Pulsed Laser-Induced Charge Generation. IEEE Transactions on Nuclear Science, 2021, 68, 626-633.	1.2	5
20	Single-Event Transient Response of Vertical and Lateral Waveguide-Integrated Germanium Photodiodes. IEEE Transactions on Nuclear Science, 2021, 68, 801-806.	1.2	7
21	A System-Level Modeling Approach for Simulating Radiation Effects in Successive-Approximation Analog-to-Digital Converters. IEEE Transactions on Nuclear Science, 2021, 68, 1465-1472.	1.2	2
22	Effects of Breakdown Voltage on Single-Event Burnout Tolerance of High-Voltage SiC Power MOSFETs. IEEE Transactions on Nuclear Science, 2021, 68, 1430-1435.	1.2	28
23	Effects of Charge Generation and Trapping on the X-ray Response of Strained AlGaN/GaN HEMTs. , 2021, , .		1
24	Radiation Effects and Low-Frequency Noise in AlGaN/GaN HEMTs. , 2021, , .		0
25	Comparison of Sensitive Volumes Associated With Ion- and Laser-Induced Charge Collection in an Epitaxial Silicon Diode. IEEE Transactions on Nuclear Science, 2020, 67, 57-62.	1.2	5
26	Unifying Concepts for Ion-Induced Leakage Current Degradation in Silicon Carbide Schottky Power Diodes. IEEE Transactions on Nuclear Science, 2020, 67, 135-139.	1.2	19
27	Total-Ionizing-Dose Effects on InGaAs FinFETs With Modified Gate-stack. IEEE Transactions on Nuclear Science, 2020, 67, 253-259.	1.2	13
28	Polarization Dependence of Pulsed Laser-Induced SEEs in SOI FinFETs. IEEE Transactions on Nuclear Science, 2020, 67, 38-43.	1.2	8
29	Total-Ionizing-Dose Effects and Low-Frequency Noise in 16-nm InGaAs FinFETs With HfO₂/Al₂O₃ Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 210-220.	1.2	26
30	Ion-Induced Energy Pulse Mechanism for Single-Event Burnout in High-Voltage SiC Power MOSFETs and Junction Barrier Schottky Diodes. IEEE Transactions on Nuclear Science, 2020, 67, 22-28.	1.2	67
31	The Impact of Proton-Induced Single Events on Image Classification in a Neuromorphic Computing Architecture. IEEE Transactions on Nuclear Science, 2020, 67, 108-115.	1.2	10
32	Development of a Flight-Program-Ready Radiation Model-Based Assurance Platform. , 2020, , .		2
33	Inclusion of Radiation Environment Variability for Reliability Estimates for SiC Power MOSFETs. IEEE Transactions on Nuclear Science, 2020, 67, 353-357.	1.2	11
34	Total-Ionizing-Dose Effects and Low-Frequency Noise in 30-nm Gate-Length Bulk and SOI FinFETs With SiO₂/HfO₂Gate Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 245-252.	1.2	29
35	DFF Layout Variations in CMOS SOIâ€"Analysis of Hardening by Design Options. IEEE Transactions on Nuclear Science, 2020, 67, 1125-1132.	1.2	3
36	Total-Ionizing-Dose Effects on 3D Sequentially Integrated, Fully Depleted Silicon-on-Insulator MOSFETs. IEEE Electron Device Letters, 2020, 41, 637-640.	2.2	12

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37	Total-Ionizing-Dose Effects in InGaAs MOSFETs With High-<i>k</i> Gate Dielectrics and InP Substrates. IEEE Transactions on Nuclear Science, 2020, 67, 1312-1319.	1.2	4
38	Charge Transport in Vertical GaN Schottky Barrier Diodes: A Refined Physical Model for Conductive Dislocations. IEEE Transactions on Electron Devices, 2020, 67, 841-846.	1.6	21
39	Worst-Case Bias for High Voltage, Elevated-Temperature Stress of AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2020, 20, 420-428.	1.5	12
40	Sensitive-Volume Model of Single-Event Latchup for a 180-nm SRAM Test Structure. IEEE Transactions on Nuclear Science, 2020, 67, 2015-2020.	1.2	3
41	Defect Dehydrogenation in Si-MOS and Compound-Semiconductor-Based Devices. , 2020, , .		1
42	Enhanced Charge Collection in SiC Power MOSFETs Demonstrated by Pulse-Laser Two-Photon Absorption SEE Experiments. IEEE Transactions on Nuclear Science, 2019, 66, 1694-1701.	1.2	19
43	Simulation of Transistor-Level Radiation Effects on System-Level Performance Parameters. IEEE Transactions on Nuclear Science, 2019, 66, 1634-1641.	1.2	5
44	Dopant-Type and Concentration Dependence of Total-Ionizing-Dose Response in Piezoresistive Micromachined Cantilevers. IEEE Transactions on Nuclear Science, 2019, 66, 397-404.	1.2	1
45	Estimating Terrestrial Neutron-Induced SEB Cross Sections and FIT Rates for High-Voltage SiC Power MOSFETs. IEEE Transactions on Nuclear Science, 2019, 66, 337-343.	1.2	37
46	Gate Bias and Length Dependences of Total Ionizing Dose Effects in InGaAs FinFETs on Bulk Si. IEEE Transactions on Nuclear Science, 2019, 66, 1599-1605.	1.2	17
47	Low-frequency noise and defects in copper and ruthenium resistors. Applied Physics Letters, 2019, 114, .	1.5	13
48	Comparison of Total-Ionizing-Dose Effects in Bulk and SOI FinFETs at 90 and 295 K. IEEE Transactions on Nuclear Science, 2019, 66, 911-917.	1.2	17
49	Electron Transport Properties of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:msub><mml:mi>Al</mml:mi><mml:mi>x</mml:mi></mml:msub><mml:msub><mml:mi>Ga</mml:mi><mml:mr mathvariant="normal">N</mml:mi></mml:mrow></mml:mrow><mml:mo>/</mml:mo><mml:mrow><mml:mi>Ga</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:mrow></mml:math> Transistors Based on F. Physical Review Applied, 2019, 11, .	1.5	23
50	Probing heavy ion radiation effects in silicon carbide (SiC) via 3D integrated multimode vibrating diaphragms. Applied Physics Letters, 2019, 114, .	1.5	7
51	Damage Separation in a Bipolar Junction Transistor Following Irradiation With 250-MeV Protons. IEEE Transactions on Nuclear Science, 2019, 66, 795-800.	1.2	5
52	Monte Carlo Simulation of Displacement Damage in Graphene. IEEE Transactions on Nuclear Science, 2019, 66, 1730-1737.	1.2	3
53	Understanding the Average Electronâ€"Hole Pair-Creation Energy in Silicon and Germanium Based on Full-Band Monte Carlo Simulations. IEEE Transactions on Nuclear Science, 2019, 66, 444-451.	1.2	16
54	Total Ionizing Dose Effects and Proton-Induced Displacement Damage on MoS₂-Interlayer-MoS₂Tunneling Junctions. IEEE Transactions on Nuclear Science, 2019, 66, 420-427.	1.2	6

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55	Laser-Induced Single-Event Transients in Black Phosphorus MOSFETs. IEEE Transactions on Nuclear Science, 2019, 66, 384-388.	1.2	3
56	Pulsed-Laser Induced Single-Event Transients in InGaAs FinFETs on Bulk Silicon Substrates. IEEE Transactions on Nuclear Science, 2019, 66, 376-383.	1.2	8
57	Using MRED to Screen Multiple-Node Charge-Collection Mitigated SOI Layouts. IEEE Transactions on Nuclear Science, 2019, 66, 233-239.	1.2	6
58	Methodology for Identifying Radiation Effects in Robotic Systems With Mechanical and Control Performance Variations. IEEE Transactions on Nuclear Science, 2019, 66, 184-189.	1.2	2
59	Total-Ionizing-Dose Response of MoS₂Transistors With ZrO₂and h-BN Gate Dielectrics. IEEE Transactions on Nuclear Science, 2019, 66, 1584-1591.	1.2	6
60	Dose-Rate Dependence of the Total-Ionizing-Dose Response of GaN-Based HEMTs. IEEE Transactions on Nuclear Science, 2019, 66, 170-176.	1.2	24
61	Pulsed Laser-Induced Single-Event Transients in InGaAs FinFETs with sub-10-nm Fin Widths. , 2019, , .		1
62	Single-Event Burnout of SiC Junction Barrier Schottky Diode High-Voltage Power Devices. IEEE Transactions on Nuclear Science, 2018, 65, 256-261.	1.2	63
63	Dose-Rate Effects on the Total-Ionizing-Dose Response of Piezoresistive Micromachined Cantilevers. IEEE Transactions on Nuclear Science, 2018, 65, 58-63.	1.2	4
64	Defects and Low-Frequency Noise in Irradiated Black Phosphorus MOSFETs With HfO₂ Gate Dielectrics. IEEE Transactions on Nuclear Science, 2018, 65, 1227-1238.	1.2	39
65	Total-Ionizing-Dose Response of Nb₂O₅-Based MIM Diodes for Neuromorphic Computing Applications. IEEE Transactions on Nuclear Science, 2018, 65, 78-83.	1.2	4
66	Analysis of TPA Pulsed-Laser-Induced Single-Event Latchup Sensitive-Area. IEEE Transactions on Nuclear Science, 2018, 65, 502-509.	1.2	6
67	Application of a Focused, Pulsed X-ray Beam for Total Ionizing Dose Testing of Bipolar Linear Integrated Circuits. IEEE Transactions on Nuclear Science, 2018, 65, 478-485.	1.2	3
68	Capacitanceâ€“Frequency Estimates of Border-Trap Densities in Multifin MOS Capacitors. IEEE Transactions on Nuclear Science, 2018, 65, 175-183.	1.2	12
69	Predicting Muon-Induced SEU Rates for a 28-nm SRAM Using Protons and Heavy Ions to Calibrate the Sensitive Volume Model. IEEE Transactions on Nuclear Science, 2018, 65, 712-718.	1.2	18
70	Correlation of a Bipolar-Transistor-Based Neutron Displacement Damage Sensor Methodology With Proton Irradiations. IEEE Transactions on Nuclear Science, 2018, 65, 495-501.	1.2	5
71	Scaling Effects on Single-Event Transients in InGaAs FinFETs. IEEE Transactions on Nuclear Science, 2018, 65, 296-303.	1.2	18
72	X-Ray and Proton Radiation Effects on 40 nm CMOS Physically Unclonable Function Devices. IEEE Transactions on Nuclear Science, 2018, 65, 1519-1524.	1.2	9

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73	Influence of LDD Spacers and H⁺Transport on the Total-Ionizing-Dose Response of 65-nm MOSFETs Irradiated to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2018, 65, 164-174.	1.2	73
74	Radiation-Induced Charge Trapping and Low-Frequency Noise of Graphene Transistors. IEEE Transactions on Nuclear Science, 2018, 65, 156-163.	1.2	15
75	Proton-Induced Displacement Damage and Total-Ionizing-Dose Effects on Silicon-Based MEMS Resonators. IEEE Transactions on Nuclear Science, 2018, 65, 34-38.	1.2	7
76	Fast Ionization-Front-Induced Anomalous Switching Behavior in Trigger Bipolar Transistors of Marx-Bank Circuits Under Base-Drive Conditions. IEEE Transactions on Plasma Science, 2018, 46, 2064-2071.	0.6	1
77	Dose-Rate Sensitivity of 65-nm MOSFETs Exposed to Ultrahigh Doses. IEEE Transactions on Nuclear Science, 2018, 65, 1482-1487.	1.2	28
78	Single-Event Burnout Mechanisms in SiC Power MOSFETs. IEEE Transactions on Nuclear Science, 2018, 65, 1951-1955.	1.2	94
79	Failure Estimates for SiC Power MOSFETs in Space Electronics. Aerospace, 2018, 5, 67.	1.1	23
80	Total-Ionizing-Dose Effects on Al/SiO2 Bimorph Electrothermal Microscanners. IEEE Transactions on Nuclear Science, 2018, 65, 2260-2267.	1.2	0
81	A TCAD evaluation of a single Bulk-BICS with integrative memory cell. Microelectronics Journal, 2018, 80, 62-68.	1.1	2
82	Molecular Dynamics Simulations of Heavy Ion Induced Defects in SiC Schottky Diodes. IEEE Transactions on Device and Materials Reliability, 2018, 18, 481-483.	1.5	12
83	Multiple Defects Cause Degradation After High Field Stress in AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2018, 18, 364-376.	1.5	49
84	Parasitic Bipolar Action in SiC Power MOSFETs Demonstrated by Two-Photon Laser Experiment. , 2018, , .		0
85	Total-Ionizing-Dose Effects in Piezoresistive Micromachined Cantilevers. IEEE Transactions on Nuclear Science, 2017, 64, 263-268.	1.2	10
86	Total-Ionizing-Dose Effects on Piezoelectric Micromachined Ultrasonic Transducers. IEEE Transactions on Nuclear Science, 2017, 64, 233-238.	1.2	2
87	Heavy Ion Induced Degradation in SiC Schottky Diodes: Bias and Energy Deposition Dependence. IEEE Transactions on Nuclear Science, 2017, 64, 415-420.	1.2	63
88	Dependence of Ideality Factor in Lateral PNP Transistors on Surface Carrier Concentration. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	12
89	Understanding Charge Collection Mechanisms in InGaAs FinFETs Using High-Speed Pulsed-Laser Transient Testing With Tunable Wavelength. IEEE Transactions on Nuclear Science, 2017, 64, 2069-2078.	1.2	17
90	CubeSats and Crowd-Sourced Monitoring for Single Event Effects Hardness Assurance. IEEE Transactions on Nuclear Science, 2017, 64, 293-300.	1.2	4

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91	Tools for modeling radioactive contaminants in chip materials. Semiconductor Science and Technology, 2017, 32, 034001.	1.0	0
92	Heavy Ion Induced Degradation in SiC Schottky Diodes: Incident Angle and Energy Deposition Dependence. IEEE Transactions on Nuclear Science, 2017, , 1-1.	1.2	20
93	CubeSat: Real-time soft error measurements at low earth orbits. , 2017, , .		3
94	Strong Correlation Between Experiment and Simulation for Two-Photon Absorption Induced Carrier Generation. IEEE Transactions on Nuclear Science, 2017, 64, 1133-1136.	1.2	14
95	Total Ionizing Dose Effects on Strained Ge pMOS FinFETs on Bulk Si. IEEE Transactions on Nuclear Science, 2017, 64, 226-232.	1.2	28
96	Worst-Case Bias for Proton and 10-keV X-Ray Irradiation of AlGaN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2017, 64, 218-225.	1.2	46
97	1/ f Noise in As-Processed and Proton-Irradiated AlGaN/GaN HEMTs Due to Carrier Number Fluctuations. IEEE Transactions on Nuclear Science, 2017, 64, 181-189.	1.2	31
98	Ionizing Dose-Tolerant Enhancement-Mode Cascode for High-Voltage Power Devices. IEEE Transactions on Nuclear Science, 2017, 64, 382-387.	1.2	2
99	The study of radiation effects in emerging micro and nano electro mechanical systems (M and NEMs). Semiconductor Science and Technology, 2017, 32, 013005.	1.0	27
100	Radiation Response and Adaptive Control-Based Degradation Mitigation of MEMS Accelerometers in Ionizing Dose Environments. IEEE Sensors Journal, 2017, 17, 1132-1143.	2.4	8
101	Charge-Steering Latch Design in 16 nm FinFET Technology for Improved Soft Error Hardness. IEEE Transactions on Nuclear Science, 2017, 64, 353-358.	1.2	9
102	Memristive devices from ZnO nanowire bundles and meshes. Applied Physics Letters, 2017, 111, .	1.5	11
103	Persistent Laser-Induced Leakage in a 20 nm Charge-Pump Phase-Locked Loop (PLL). IEEE Transactions on Nuclear Science, 2017, 64, 512-518.	1.2	5
104	Total Ionizing Dose Effects on HfO₂-Passivated Black Phosphorus Transistors. IEEE Transactions on Nuclear Science, 2017, 64, 170-175.	1.2	19
105	Gate Bias and Geometry Dependence of Total-Ionizing-Dose Effects in InGaAs Quantum-Well MOSFETs. IEEE Transactions on Nuclear Science, 2017, 64, 239-244.	1.2	17
106	Displacement Damage in Bipolar Junction Transistors: Beyond Messenger-Spratt. IEEE Transactions on Nuclear Science, 2017, 64, 149-155.	1.2	26
107	1.8 MeV Proton Testing of Thermally Stabilized GaN HEMT RF Power Devices in Three Operational Modes. , 2017, , .		0
108	Bayesian Modeling of COTS Power MOSFET Ionizing Dose Impact on Circuit Response. , 2017, , .		3

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109	RadFxSat: A Flight Campaign for Recording Single-Event Effects in Commercial Off-the-Shelf Microelectronics. , 2017, , .		2
110	1/f noise in GaN/AlGaN HEMTs. , 2016, , .		2
111	Incident angle effect on heavy ion induced reverse leakage current in SiC Schottky diodes. , 2016, , .		5
112	Total ionizing dose effects in passivated and unpassivated AlGaN/GaN HEMTs. , 2016, , .		4
113	High-Field Stress, Low-Frequency Noise, and Long-Term Reliability of AlGaN/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 282-289.	1.5	25
114	Charge Transport Mechanisms in Heavy-Ion Driven Leakage Current in Silicon Carbide Schottky Power Diodes. IEEE Transactions on Device and Materials Reliability, 2016, 16, 208-212.	1.5	27
115	Correlation of proton irradiation induced threshold voltage shifts to deep level traps in AlGaN/GaN heterostructures. Journal of Applied Physics, 2016, 119, .	1.1	35
116	Modeling Erratic Behavior Due to High Current Filamentation in Bipolar Structures Under Dynamic Avalanche Conditions. IEEE Transactions on Electron Devices, 2016, , 1-8.	1.6	4
117	Degradation and annealing effects caused by oxygen in AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2016, 109, .	1.5	22
118	Effects of Negative-Bias-Temperature-Instability on Low-Frequency Noise in SiGe ${p}$ MOSFETs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 541-548.	1.5	16
119	Electrical Effects of a Single Extended Defect in MOSFETs. IEEE Transactions on Electron Devices, 2016, 63, 3069-3075.	1.6	9
120	Estimation of single-event transient pulse characteristics for predictive analysis. , 2016, , .		4
121	Temperature dependence of soft-error rates for FF designs in 20-nm bulk planar and 16-nm bulk FinFET technologies. , 2016, , .		24
122	Introduction of Interfacial Charges to Black Phosphorus for a Family of Planar Devices. Nano Letters, 2016, 16, 6870-6878.	4.5	69
123	Pulsed-laser transient testing with tunable wavelength and high resolution for high mobility MOSFETs. , 2016, , .		0
124	On the assessment of electrically active defects in high-mobility materials and devices. , 2016, , .		0
125	Hot-Carrier Degradation in GaN HEMTs Due to Substitutional Iron and Its Complexes. IEEE Transactions on Electron Devices, 2016, 63, 1486-1494.	1.6	27
126	Thermal stability of deep level defects induced by high energy proton irradiation in n-type GaN. Journal of Applied Physics, 2015, 118, .	1.1	23

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127	Efficient Reliability Testing of Emerging Memory Technologies Using Multiple Radiation Sources. Physics Procedia, 2015, 66, 568-575.	1.2	0
128	Proton irradiation-induced traps causing V<inf>T</inf> instabilities and RF degradation in GaN HEMTs. , 2015, , .		5
129	Rapid non-destructive detection of sub-surface Cu in silicon-on-insulator wafers by optical second harmonic generation. , 2015, , .		1
130	Bayesian Inference Modeling of Total Ionizing Dose Effects on System Performance. IEEE Transactions on Nuclear Science, 2015, 62, 2517-2524.	1.2	5
131	Charge Collection Mechanisms of Ge-Channel Bulk <formula formulatype="inline"><tex Notation="TeX">p</tex> </formula>MOSFETs. IEEE Transactions on Nuclear Science, 2015, 62, 2725-2731.	1.2	8
132	SEB Hardened Power MOSFETs With High-K Dielectrics. IEEE Transactions on Nuclear Science, 2015, 62, 2830-2836.	1.2	24
133	Total Ionizing Dose Effects on Ge Channel <formula formulatype="inline"><tex Notation="TeX">p</tex></formula>FETs with Raised <formula formulatype="inline"><tex Notation="TeX">${m Si}_{0.55}{m Ge}_{0.45}$</tex></formula> Source/Drain. IEEE Transactions on Nuclear Science, 2015, 62, 2412-2416.	1.2	7
134	Estimation of Single-Event-Induced Collected Charge for Multiple Transistors Using Analytical Expressions. IEEE Transactions on Nuclear Science, 2015, 62, 2853-2859.	1.2	3
135	Proton Irradiation as a Screen for Displacement-Damage Sensitivity in Bipolar Junction Transistors. IEEE Transactions on Nuclear Science, 2015, 62, 2498-2504.	1.2	8
136	Vanderbilt Pelletron - Low Energy Protons and Other Ions for Radiation Effects on Electronics. , 2015, , .		14
137	Electron-Induced Single Event Upsets in 28Ânm and 45Ânm Bulk SRAMs. IEEE Transactions on Nuclear Science, 2015, 62, 2709-2716.	1.2	23
138	Effects of Applied Bias and High Field Stress on the Radiation Response of GaN/AlGaN HEMTs. IEEE Transactions on Nuclear Science, 2015, 62, 2423-2430.	1.2	84
139	Two-Photon Absorption Induced Single-Event Effects: Correlation Between Experiment and Simulation. IEEE Transactions on Nuclear Science, 2015, 62, 2867-2873.	1.2	18
140	Charge Collection Mechanisms in GaAs MOSFETs. IEEE Transactions on Nuclear Science, 2015, 62, 2752-2759.	1.2	10
141	Effects of Proton-Induced Displacement Damage on Gallium Nitride HEMTs in RF Power Amplifier Applications. IEEE Transactions on Nuclear Science, 2015, 62, 2417-2422.	1.2	53
142	Proton irradiation effects on deep level states in Mg-doped p-type GaN grown by ammonia-based molecular beam epitaxy. Applied Physics Letters, 2015, 106, .	1.5	32
143	Self-Healing of Proton Damage in Lithium Niobite (<formula formulatype="inline"><tex) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Science, 2015, 62, 542-547.	1.2	1
144	System Health Awareness in Total-Ionizing Dose Environments. IEEE Transactions on Nuclear Science, 2015, 62, 1674-1681.	1.2	2

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145	Limitations of LET in Predicting the Radiation Response of Advanced Devices. IEEE Transactions on Nuclear Science, 2015, 62, 1558-1567.	1.2	1
146	Role of Fe impurity complexes in the degradation of GaN/AlGaN high-electron-mobility transistors. Applied Physics Letters, 2015, 106, .	1.5	45
147	Quantum Mechanical Modeling of Radiation-Induced Defect Dynamics in Electronic Devices. IEEE Transactions on Nuclear Science, 2015, 62, 2169-2180.	1.2	20
148	Effects of Energy-Deposition Variability on Soft Error Rate Prediction. IEEE Transactions on Nuclear Science, 2015, 62, 2181-2186.	1.2	6
149	Activation Energies for Oxide- and Interface-Trap Charge Generation Due to Negative-Bias Temperature Stress of Si-Capped SiGe-pMOSFETs. IEEE Transactions on Device and Materials Reliability, 2015, 15, 352-358.	1.5	9
150	Geometry-Aware Single-Event Enabled Compact Models for Sub-50Ânm Partially Depleted Silicon-on-Insulator Technologies. IEEE Transactions on Nuclear Science, 2015, 62, 1589-1598.	1.2	17
151	Physical Processes and Applications of the Monte Carlo Radiative Energy Deposition (MRED) Code. IEEE Transactions on Nuclear Science, 2015, 62, 1441-1461.	1.2	50
152	Influence of supply voltage on the multi-cell upset soft error sensitivity of dual- and triple-well 28 nm CMOS SRAMs. , 2015, , .		11
153	Bias Dependence of Single-Event Upsets in 16Ânm FinFET D-Flip-Flops. IEEE Transactions on Nuclear Science, 2015, 62, 2578-2584.	1.2	43
154	Physical Mechanisms Affecting the Reliability of GaN-based High Electron Mobility Transistors. Materials Research Society Symposia Proceedings, 2015, 1792, 1.	0.1	0
155	Dynamic Modeling of Radiation-Induced State Changes in <formula formulatype="inline"><tex Notation="TeX">${hbox {HfO}_2}/hbox {Hf}$</tex></formula> 1T1R RRAM. IEEE Transactions on Nuclear Science, 2014, 61, 3497-3503.	1.2	13
156	State and Angular Dependence of Single-Event Upsets in an Asymmetric RC-Hardened SRAM Using Deep Trench Capacitors. IEEE Transactions on Nuclear Science, 2014, 61, 3068-3073.	1.2	1
157	Heavy-Ion and Laser Induced Charge Collection in SiGe Channel <formula formulatype="inline"><tex Notation="TeX">$p{m MOSFETs}$</tex></formula>. IEEE Transactions on Nuclear Science, 2014, 61, 3187-3192.	1.2	15
158	Single-Event Transient Response of InGaAs MOSFETs. IEEE Transactions on Nuclear Science, 2014, 61, 3550-3556.	1.2	20
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